

# *Argonne Possible Involvement in RD50*

Some areas where the lab and division might make a contribution to RD50 objectives

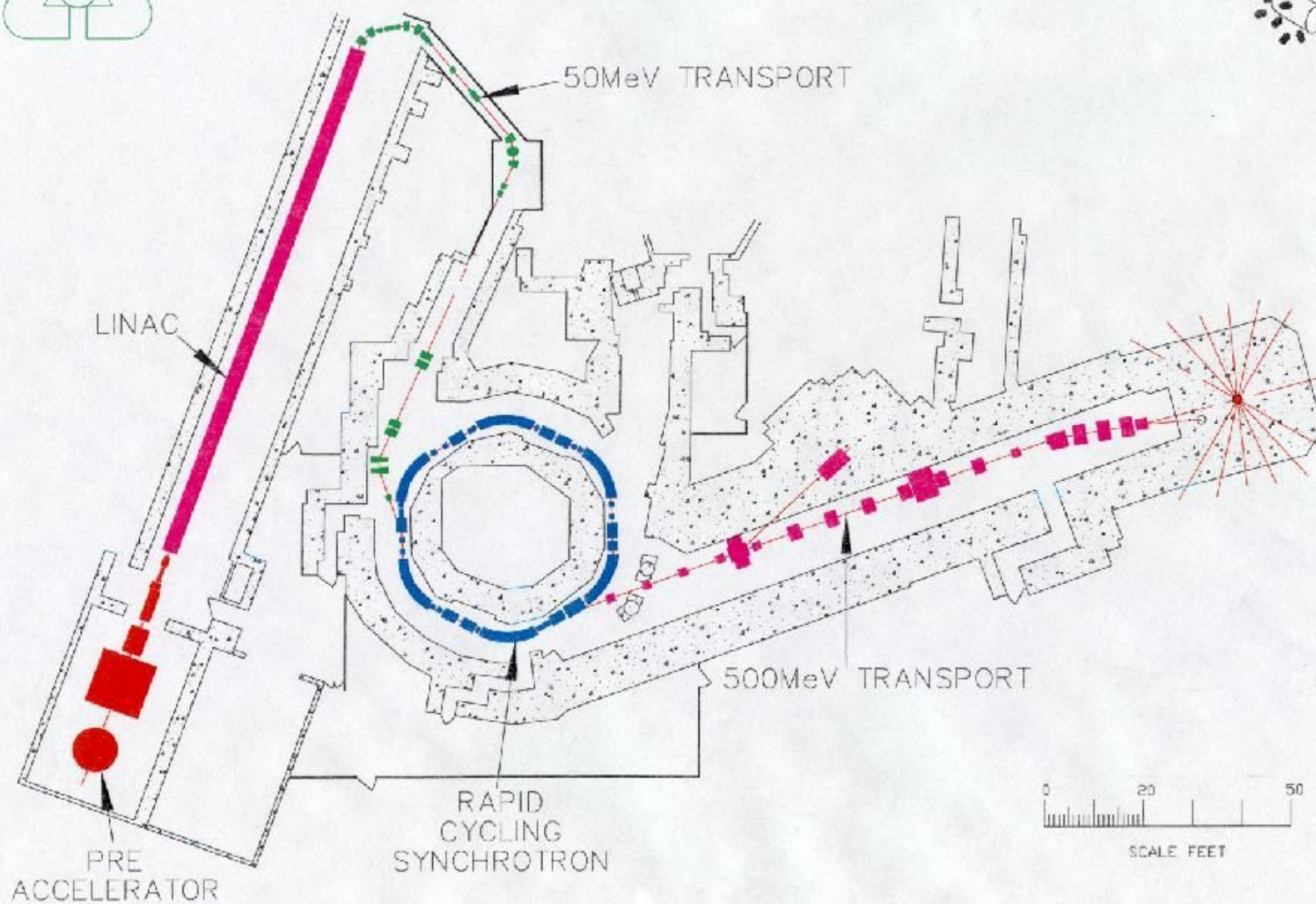
IPNS information available at:  
<http://www.pns.anl.gov>

---

---



# ACCELERATOR FACILITIES



# IPNS as a resource for RD50

- Energy  $\sim 1\text{MeV}$
- Measured exposure
- High intensity
- SSC era studies done in collab. with Penn. (see example to right)

ACR-300 NO. 90-4057

NEUTRON FLUENCES AND ACTIVITIES FOR HEP IRRADIATIONS AT IPNS-H2

Sample	Neutron Fluence $\text{n/cm}^2$	Activation Rate (at/at-s) ( $\pm\%$ )	
		$^{59}\text{Co}(\text{n}, \gamma)^{60}\text{Co}$ ( $\times 10^{-14}$ )	$^{58}\text{Ni}(\text{n}, \text{p})^{58}\text{Co}$ ( $\times 10^{-17}$ )
35	$4.21 \times 10^{11}$	13.5 (7.0)	10.5 (8.0)
36	$2.43 \times 10^{11}$	7.39 (8.0)	6.49 (10.0)
37	$9.23 \times 10^{12}$	69.4 (5.0)	109 (5.0)
38	$6.55 \times 10^{12}$	63.0 (5.0)	62.5 (5.0)
39	$6.08 \times 10^{13}$	149 (5.0)	141 (5.0)
40	$8.00 \times 10^{13}$	169 (5.0)	216 (5.0)
41	$1.01 \times 10^{14}$	173 (5.0)	317 (5.0)

The neutron fluences for the dosimeter wires from your IPNS-H2 irradiation on 11/7/89 are shown in the above table; these values were determined as outlined in L. Greenwood's memo of 6/2/89. The absolute uncertainties in these fluences are 15%.

The uncertainties for the activation rates are propagated from the relative difference between duplicate counts with an added 2% to account for calibration uncertainties.

# *Center for Nanoscale Material*

## Nano- and Microlithography

Nano- and microlithography capabilities are key to top-down fabrication of nanostructures. Acquisition of powerful new state-of-the-art tools is planned. Among these tools are a 100-kV electron-beam lithography tool, reactive ion etch tools, a cross-beam-focused ion beam tool, and advanced metrology tools. Current capabilities include

- \* Optical microlithography using a dual side contact print aligner
  - \* Small sample reactive ion etch, single chamber
  - \* JEOL 840 SEM with a beam blanker and Raith Elphys software
  - \* Raith 150 low-voltage electron-beam lithography tool (September 2003)
  - \* Access to a JEOL JBX-6000FS 50-kV electron-beam tool at the University of Illinois at Urbana-Champaign
  - \* Access to a JEOL JBX-9300FS 100-kV electron-beam tool at the New Jersey Nanotechnology Consortium
- 
-